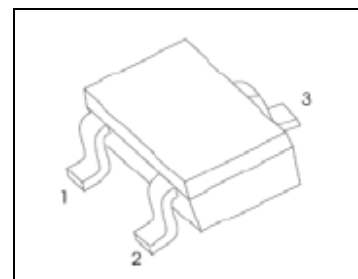
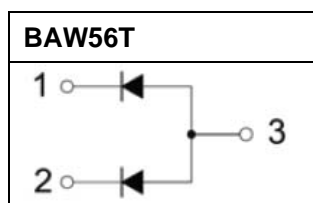
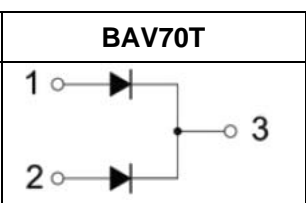
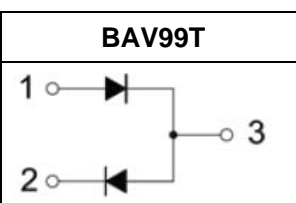
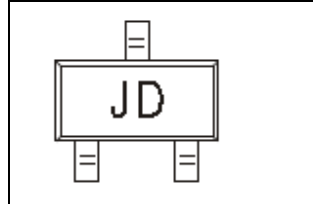
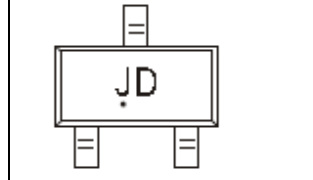
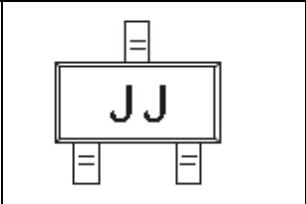
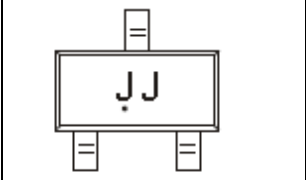
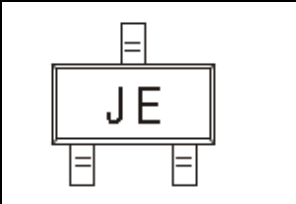
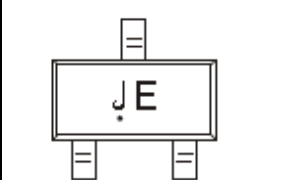


BAW56T/BAV70T/BAV99T SWITCHING DIODE

Features:

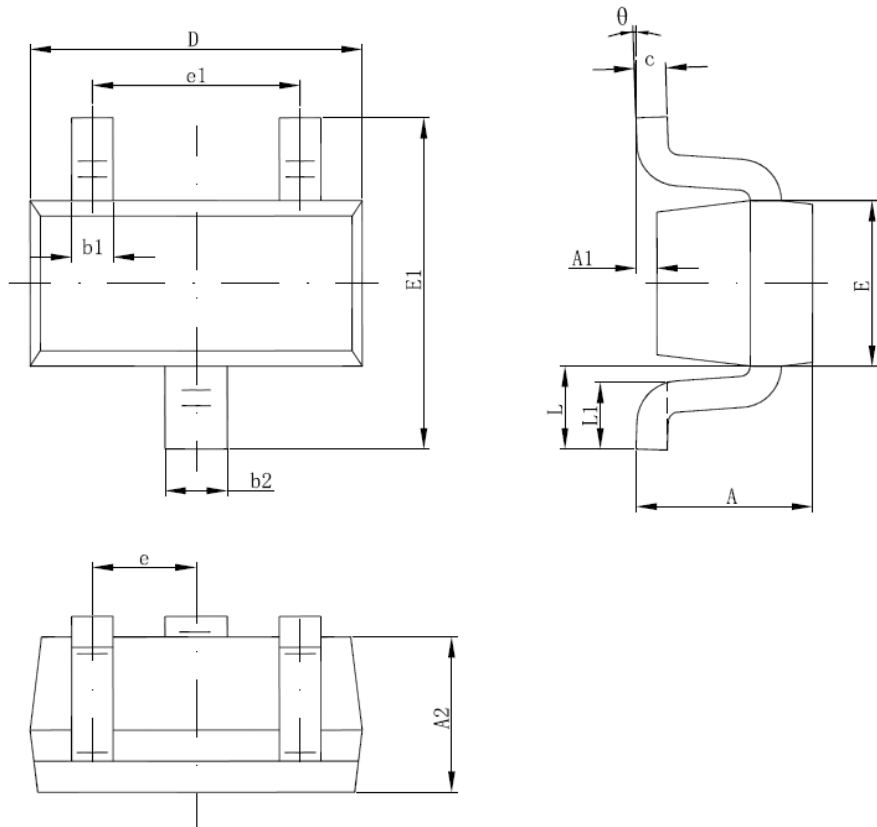
- Low Forward Voltage Drop
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection



BAW56T	BAV70T	BAV99T
		
MARKING:JD	MARKING:JJ	MARKING:JE
 	 	 

Solid dot = Green molding compound device, if none, the normal device.

Mechanical Dimensions: In mm/Inches



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523

Ordering Information:

Device	Package	Shipping
BAW56T/BAV70T/BAV99T	SOT-523(Pb-Free)	3000pcs / reel

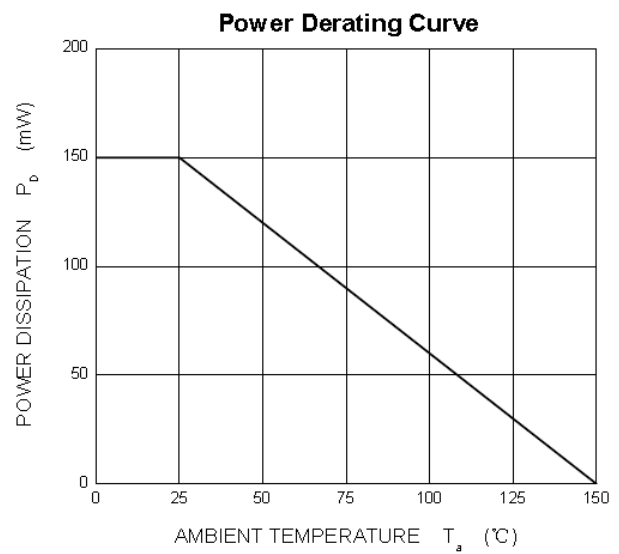
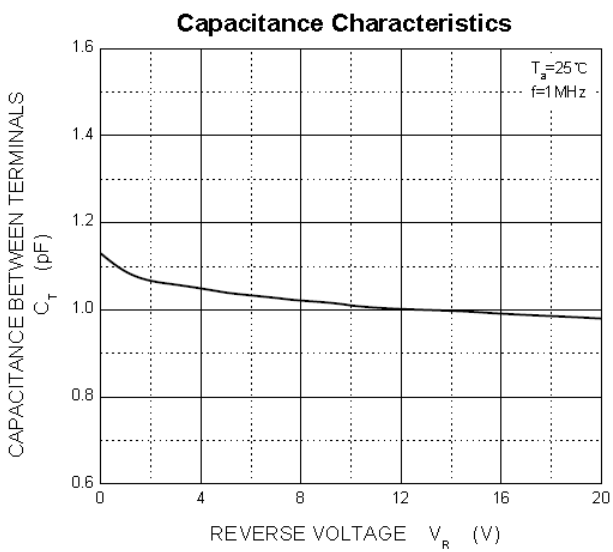
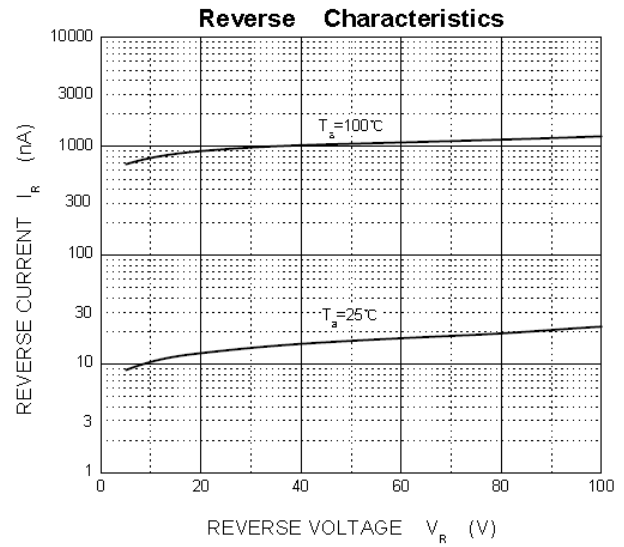
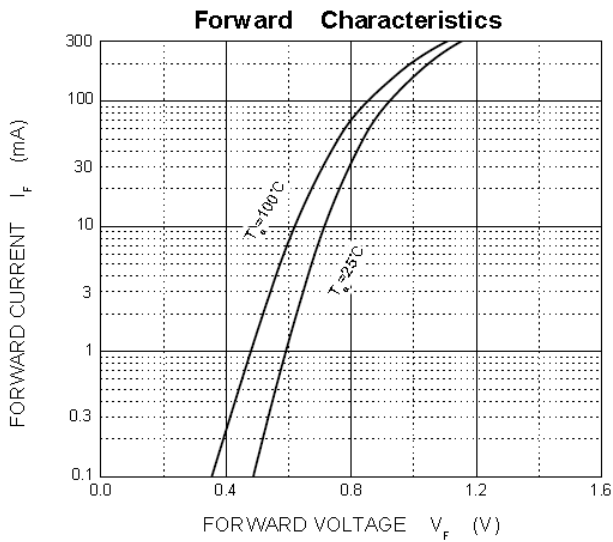
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	85	V
Forward Current	I_F	75	mA
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	2.0	A
Power Dissipation	P_D	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\mu\text{A}$	85	-	V
Reverse voltage leakage current	I_{R1}	$V_R=75\text{V}$	-	2	μA
		$V_R=25\text{V}$	-	0.03	μA
Forward voltage	V_F	$I_F=1\text{mA}$	-	715	mV
		$I_F=10\text{mA}$	-	855	
		$I_F=50\text{mA}$	-	1000	
		$I_F=150\text{mA}$	-	1250	
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$	-	1.5	pF
Reverse recovery time	T_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=0.1\times I_R, R_L=100\Omega$	-	4	ns





BAW56T
BAV70T
BAV99T

Technical Data
Data Sheet N1727, Rev. -

Green Products

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